

Customer No.: 31561
Docket No.:12041-US-PA
Application No.: 10/707,110

REMARKS

Present Status of the Application

Claims 1-12 have been allowed. The Office Action rejected claims 13-17 under 35 U.S.C. 102(e), as being anticipated by Lin et al. (U.S. 2004/0188685 A1). Applicants have amended claim 13 to improve clarity. After entry of the foregoing amendments, claims 1-17 remain pending in the present application, and reconsideration of those claims is respectfully requested.

Discussion of Office Action Rejections

The Office Action rejected claim 13 under 35 U.S.C. 102(e), as being anticipated by Lin et al. (U.S. 2004/0188685 A1). Applicants, however, respectfully submit that Lin et al. is legally deficient to render claim 13 unpatentable. Also, Applicants respectfully traverse this rejection but have amended claim 13 to clearly define the structure according to the invention. As amended, claim 13 recites:

13. A pixel structure of an active organic light emitting diode, comprising:
an organic light emitting diode;
a data-line;
a scan-line;
a switch thin film transistor having a first gate terminal, a first source terminal, a first drain terminal and a *lightly doped drain region*, wherein the first gate terminal is coupled to the scan-line and the first drain terminal is coupled to the data-line;
a control thin film transistor having a second gate terminal, a second source terminal and a second drain terminal, wherein the second gate terminal is coupled to the first source terminal and the second drain terminal is coupled to the organic light emitting diode; and
a capacitor coupled to the first drain terminal and to the second gate terminal.

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(Emphasis Added) Applicants submit that the claim patently defines over the prior art of record, for at least the reason that the prior arts fail to disclose at least the element emphasized above.

In the cited art, Lin et al. do not disclose a substantial lightly doped drain region, and only disclose “the thin film transistor formed accordingly is constructed like a perpendicular type of lightly doped drain”([0040] and [0052] in the cited art). However, in claim 13 of the present invention, a lightly doped drain region is substantially formed in the switch thin film transistor. Therefore, the cited art is different from the present invention, so that Lin et al. do not disclose claim 13 of the present invention.

Furthermore, the futures of the present invention include the doped concentration of the second lightly doped drain terminal is higher than that of the first lightly doped drain region, the first lightly doped drain terminal is longer than the second lightly doped drain region, or the lightly doped drain region is only formed within the switch thin film transistor([0016], [0028], [0029] in the present invention). However, in the cited art, Lin et al. do not disclose the relation between the lightly doped drain regions in the switch thin film transistor and the control thin film transistor. Accordingly, claim 13 could not be anticipated by Lin et al.

For at least the foregoing reasons, Applicant respectfully submits that independent claim 13 patently define over the prior art references, and should be allowed. For at least the same reasons, dependent claims 14-17 patently define over the prior art as well.

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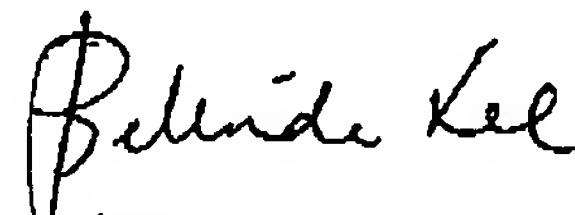
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CONCLUSION

For at least the foregoing reasons, it is believed that the pending claims 1-17 are in proper condition for allowance. If the Examiner believes that a telephone conference would expedite the examination of the above-identified patent application, the Examiner is invited to call the undersigned.

Respectfully submitted,

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